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July 1998

DS36276 FAILSAFE Multipoint Transceiver

National Semiconductor

### DS36276 FAILSAFE Multipoint Transceiver

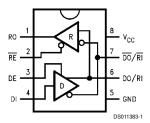
#### **General Description**

The DS36276 FAILSAFE Multipoint Transceiver is designed for use on bi-directional differential busses. It is compatible with existing TIA/EIA-485 transceivers, however, it offers an additional feature not supported by standard transceivers.

The FAILSAFE feature guarantees the receiver output to a known state when the Interface is in the following conditions: Floating Line, Idle Line (no active drivers), and Line Fault conditions (open or short). The receiver output is in a HIGH state for the following conditions: OPEN Inputs, Terminated Inputs ( $50\Omega$ ), and SHORTED Inputs.

FAILSAFE is a highly desirable feature when the transceivers are used with Asynchronous Controllers such as UARTs.

### Connection and Logic Diagram



Order Number DS36276M See NS Package Number M08A

#### Features

- FAILSAFE receiver, RO = HIGH for:
  - OPEN inputs
  - Terminated inputs
  - SHORTED inputs
- Compatible with popular interface standards:
  - TIA/EIA-485 (RS-485)
  - TIA/EIA-422-A (RS-422-A) — CCITT Recommendation V.11
- Bi-Directional Transceiver
- Directional transceiver
   Designed for multipoint transmission
- Separate driver input, driver enable, receiver enable, and receiver output for maximum flexibility
- Wide bus common mode range — (-7V to +12V)
- Pin compatible with: DS75176B, DS96176, DS3695 and SN75176A and B
- Available in SOIC package

#### **Truth Tables**

#### Driver

	Inputs	Outputs		
RE	DE DI		DO/RI	DO /RI
Х	н	Н	Н	L
X	н	L	L	н
X	L	Х	Z	Z

#### Receiver

	Output		
RE	DE	RI– <del>R</del> I	RO
L	L	≥0V	Н
L	L	≤–500 mV	L
Н	Х	Х	Z

#### **Receiver FAILSAFE**

	Output		
RE	DE	RO	
L	L	SHORTED	Н
L	L	OPEN	н
Н	х	x	Z

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#### Absolute Maximum Ratings (Note 1)

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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V <sub>CC</sub> )	7V
Input Voltage (DE, $\overline{RE}$ , and DI)	5.5V
Driver Output Voltage/	
Receiver Input Voltage	-10V to +15V
Receiver Output Voltage (RO)	5.5V
Maximum Package Power Dissipation	@ +25°C
M Package (derate 5.8 mW/°C above	
+25°C)	726 mW
Storage Temperature Range	–65°C to +150°C

Lead Temperature (Soldering 4	
sec.)	260°C
Max Junction Temperature	150°C
ESD Rating (HBM, 1.5 kΩ, 100	
pF)	≥ 6.0 kV

# Recommended Operating Conditions

	Min	Max	Units
Supply Voltage, V <sub>CC</sub>	4.75	5.25	V
Bus Voltage	-7	+12	V
Operating Temperature (T <sub>A</sub> )			
DS36276	0	+70	°C

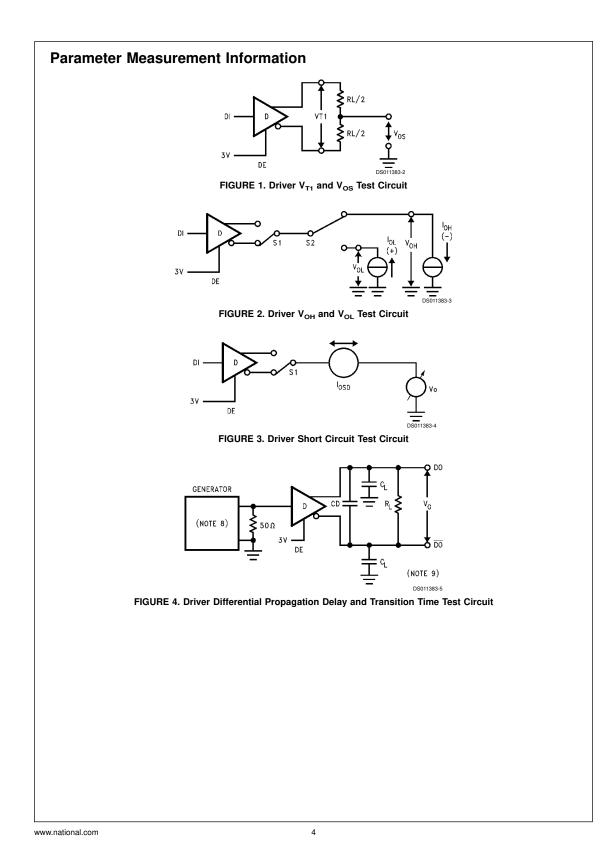
#### Electrical Characteristics (Notes 2, 4)

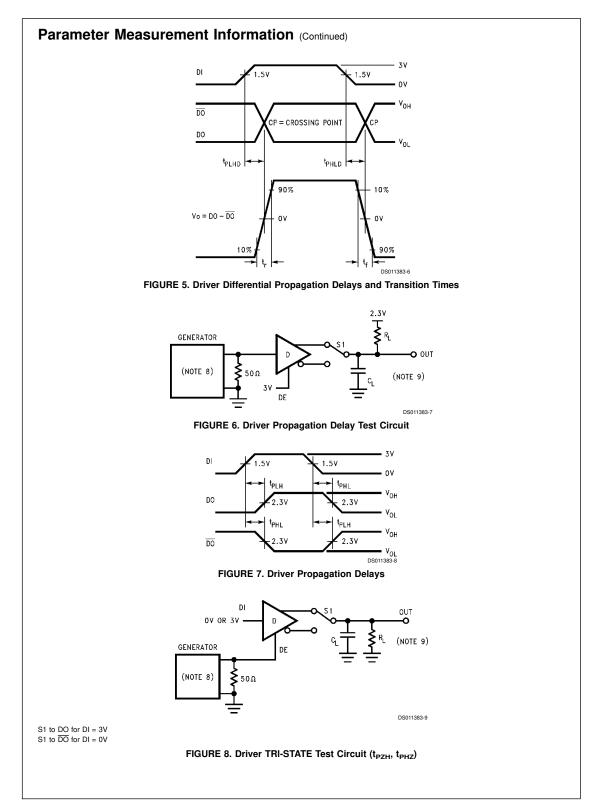
Over recommended Supply Voltage and Operating Temperature ranges, unless otherwise specified.

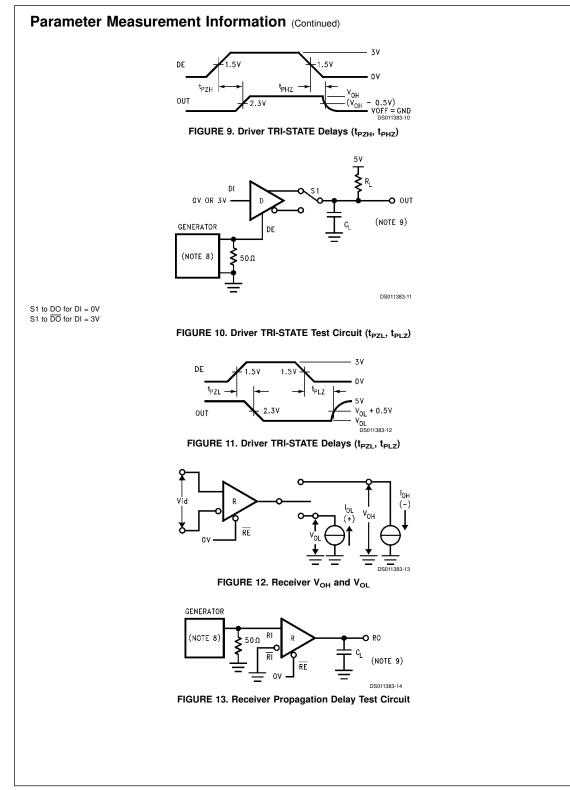
Symbol	Parameter	Conditions			Min	Тур	Max	Units
DRIVER C	HARACTERISTICS							
V <sub>OD</sub>	Differential Output Voltage	I <sub>O</sub> = 0 mA (No Load	)		1.5	4.8	6.0	V
V <sub>oDO</sub>	Output Voltage	I <sub>O</sub> = 0 mA (Output to	o GND)		0		6.0	V
V <sub>oDO</sub>	Output Voltage		0		6.0	V		
V <sub>T1</sub>	Differential Output Voltage	$R_{L} = 54\Omega$ (485)	(Figure 1)		1.5	2.0	5.0	V
	(Termination Load)	$R_{L} = 100\Omega$ (422)			2.0	2.3	5.0	V
$\Delta V_{T1}$	Balance of V <sub>T1</sub>	$R_L = 54\Omega$	(Note 3)		-0.2	0.07	+0.2	V
	$ V_{T1}  -  \overline{V}_{\overline{T1}} $	$R_L = 100\Omega$			-0.2	0.07	+0.2	V
Vos	Driver Common Mode	$R_L = 54\Omega$	(Figure 1)		0	2.5	3.0	V
	Output Voltage	$R_L = 100\Omega$	]		0	2.3	3.0	V
$\Delta V_{OS}$	Balance of V <sub>OS</sub>	$R_L = 54\Omega$	(Note 3)		-0.2	0.08	+0.2	V
	$ V_{OS}  -  \overline{V}_{OS} $	R <sub>L</sub> = 100Ω	1		-0.2	0.08	+0.2	V
IOSD	Driver Short-Circuit	V <sub>O</sub> = +12V	(Figure 3)			134	290	mA
	Output Current	$V_{\rm O} = V_{\rm CC}$	1			140		mA
		$V_{\rm O} = 0V$	1			-140		mA
		$V_{O} = -7V$	1			-180	-290	mA
RECEIVE	R CHARACTERISTICS							
$V_{TH}$	Differential Input High Threshold Voltage (Note 5)	$V_{O} = V_{OH}, I_{O} = -0.4 \text{ mA}$ -7V $\leq V_{CM} \leq +12V$				-0.18	0	V
V <sub>TL</sub>	Differential Input Low Threshold Voltage (Note 5)	$V_{O} = V_{OL}, I_{O} = 8.0 \text{ r}$ -7V $\leq V_{CM} \leq +12V$	$V_{\rm O} = V_{\rm OL},  I_{\rm O} = 8.0   {\rm mA}$			-0.23		V
V <sub>HST</sub>	Hysteresis (Note 6)	$V_{CM} = 0V$				50		mV
I <sub>IN</sub>	Line Input Current	Other Input = 0V	V <sub>I</sub> = +12V			0.7	1.0	mA
	(V <sub>CC</sub> = 4.75V, 5.25V, 0V)	DE = V <sub>IH</sub> (Note 7)	$V_1 = -7V$			-0.5	-0.8	mA
I <sub>OSR</sub>	Short Circuit Current	$V_{O} = 0V$		RO	-5.0	-30	-85	mA
l <sub>oz</sub>	TRI-STATE <sup>®</sup> Leakage Current	V <sub>O</sub> = 0.4 to 2.4V	0		-20		+20	μA
V <sub>OH</sub>	Output High Voltage	$V_{ID} = 0V, I_{OH} = -0.4$	$V_{ID} = 0V, I_{OH} = -0.4 \text{ mA}$		2.5	3.5		V
	(Figure 12)	V <sub>ID</sub> = OPEN, I <sub>OH</sub> =	–0.4 mA	1	2.5	3.5		V
V <sub>OL</sub>	Output Low Voltage	$V_{ID} = -0.5V, I_{OL} = +$	-8 mA	1		0.25	0.6	V
	(Figure 12)	$V_{ID} = -0.5V, I_{OL} = +$	-16 mA	1		0.35	0.7	V
R <sub>IN</sub>	Input Resistance				12	19		kΩ

ACTERISTICS the Level Input Voltage w Level Input Voltage the Level Input Current w Level Input Current w Level Input Current to Clamp Voltage tput Low Voltage pply Current to Load) Characteristics (Interpreted and Operational Construction Parameter CACTERISTICS Diff. Prop. Delay Low to High Diff. Prop. Delay High to Low	DE = 3 DE = 6 DE = 6 DE = 6 (Note 4)	$\overline{P}_{L} = 54\Omega$	s otherwise	т Т	ур	V <sub>CC</sub> 0.8 20 -100 -1.5 60 45 60 50 <b>Max</b>	V μA μA V mA mA mA mA
w Level Input Voltage the Level Input Current w Level Input Current wut Clamp Voltage tput Low Voltage pply Current b Load) the Characteristics (fill ended Supply Voltage and Oper Parameter RACTERISTICS Diff. Prop. Delay Low to High	$V_{IL} = 0$ $I_{CL} = -$ $DE = 0$ $DE = 0$ $DE = 0$ $(Note 4)$	$\overline{P}_{L} = 54\Omega$	s otherwise	GND e specifie	42 28 43 31 d.	0.8 20 -100 -1.5 60 45 60 50 <b>Max</b>	V           μA           μA           V           mA           mA           mA           mA
h Level Input Current w Level Input Current wut Clamp Voltage tput Low Voltage pply Current b Load) true Characteristics (feeded Supply Voltage and Oper Parameter RACTERISTICS Diff. Prop. Delay Low to High	$V_{IL} = 0$ $I_{CL} = -$ $DE = 0$ $DE = 0$ $DE = 0$ $(Note 4)$	$\overline{P}_{L} = 54\Omega$	s otherwise	e specifie	42 28 43 31 d.	20 -100 -1.5 60 45 60 50 80 80 80 80 80 80 80 80 80 80 80 80 80	μ μΑ V mA mA mA mA
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ut Clamp Voltage tput Low Voltage pply Current b Load) ag Characteristics (feeded Supply Voltage and Ope Parameter RACTERISTICS Diff. Prop. Delay Low to High	$V_{IL} = 0$ $I_{CL} = -$ $DE = 0$ $DE = 0$ $DE = 0$ $(Note 4)$	$\overline{P}_{L} = 54\Omega$	s otherwise	т Т	42 28 43 31 d.	-1.5 60 45 60 50 <b>Max</b>	V mA mA mA
tput Low Voltage pply Current b Load) In g Characteristics (f ended Supply Voltage and Ope Parameter RACTERISTICS Diff. Prop. Delay Low to High	DE = 3 DE = 6 DE = 6 DE = 6 (Note 4)	$\frac{3V, \overline{RE} = 0V, DI = 0V}{3V, \overline{RE} = 0V, DI = 0V}$ $\frac{3V, \overline{RE} = 3V, DI = 0V}{3V, \overline{RE} = 3V, DI = 0V}$ $\frac{1}{2}$ The momentum ranges, unless The momentum ranges, un	Min	т Т	42 28 43 31 d.	60 45 60 50 Max	mA mA mA mA
pply Current b Load)	DE = ( DE = 3 DE = ( (Note 4)	$\overline{P}$ $\overline{RE} = 0V, DI = 0V$ $\overline{3}V, \overline{RE} = 3V, DI = 0V$ $\overline{2}V, \overline{RE} = 3V, DI = 0V$ $\overline{P}$ $\overline{RE} = 3V, DI = 0V$ $\overline{Conditions}$ $\overline{R_{L}} = 54\Omega$	Min	т Т	28 43 31 d.	45 60 50 Max	mA mA mA
Diff. Prop. Delay Low to High	DE = 3 DE = 0 (Note 4)	$\frac{3V, \overline{RE} = 3V, DI = 0V}{DV, \overline{RE} = 3V, DI = 0V}$ Temperature ranges, unles Conditions $\overline{R_{L} = 54\Omega}$	Min	т Т	43 31 d. <b>yp</b>	60 50 Max	mA mA
Ig Characteristics ( ended Supply Voltage and Ope Parameter RACTERISTICS Diff. Prop. Delay Low to High	DE = (	$\overline{\text{PV}, \overline{\text{RE}}} = 3\text{V}, \text{DI} = 0\text{V}$ emperature ranges, unles <b>Conditions</b> $R_L = 54\Omega$	Min	т Т	31 d. <b>`yp</b>	50 Max	mA
ended Supply Voltage and Ope Parameter RACTERISTICS Diff. Prop. Delay Low to High	(Note 4)	emperature ranges, unles Conditions R <sub>L</sub> = 54Ω	Min	т Т	d. Typ	Max	
ended Supply Voltage and Ope Parameter RACTERISTICS Diff. Prop. Delay Low to High		Conditions $R_L = 54\Omega$	Min	т Т	ур		Units
RACTERISTICS Diff. Prop. Delay Low to High		R <sub>L</sub> = 54Ω					
Diff. Prop. Delay Low to High		-	7			· · · · ·	
1 , 0		-			21	60	ns
		C <sub>L</sub> = 50 pF	7		19	60	ns
Diff. Skew ( t <sub>PLHD</sub> –t <sub>PHLD</sub>  )		$C_D = 50 \text{ pF}$			2	10	ns
Diff. Rise Time		(Figures 4, 5)			12	50	ns
Diff. Fall Time					12	50	ns
Prop. Delay Low to High		$R_L = 27\Omega, C_L = 15 \text{ pF}$			22	45	ns
Prop. Delay High to Low		(Figures 6, 7)		:	22	45	ns
Enable Time Z to High		$R_L = 110\Omega$		;	32	55	ns
Enable Time Z to Low				;	32	65	ns
Disable Time High to Z		(Figure 8 – Figure 11)			22	55	ns
Disable Time Low to Z					16	55	ns
IARACTERISTICS							
. , ,					-	-	ns
. , ,			15			-	ns
							ns
Ū							ns
		(1190103-10, 10)					ns
8							ns ns
e Maximum Ratings"are those values be ad at these limits. The tables of "Electric nto device pins is defined as positive. Cu and $\Delta \mid V_{OS} \mid$ are changes in magnitude of	cal Charac irrent out o of V <sub>T1</sub> and	teristics" specify conditions for de f device pins is defined as negative	evice operation e. All voltages	ed. They are n. are reference	e not meant	to imply that	the devices
	Diff. Fall Time Prop. Delay Low to High Prop. Delay High to Low Enable Time Z to High Enable Time Z to Low Disable Time High to Z Disable Time Low to Z <b>ARACTERISTICS</b> Prop. Delay Low to High Prop. Delay High to Low Skew ( $ t_{PLH}-t_{PHL} $ ) Enable Time Z to High Enable Time Z to Low Disable Time Low to Z Disable Time Low to Z Disable Time Low to Z Disable Time Low to Z Invariant Ratings"are those values b d at these limits. The tables of "Electric to device pins is defined as positive. Cu are given for V <sub>CC</sub> = 5.0V and T <sub>A</sub> = d parameter limits specified as an alge s defined as V <sub>HST</sub> = V <sub>TH</sub> - V <sub>TL</sub> .	Diff. Fall Time         Prop. Delay Low to High         Prop. Delay High to Low         Enable Time Z to High         Enable Time Z to Low         Disable Time High to Z         Disable Time Low to Z         ARACTERISTICS         Prop. Delay High to Low         Skew ( $ t_{PLH}-t_{PHL} $ )         Enable Time Z to High         Enable Time Z to Low         Disable Time Z to Low         Skew ( $ t_{PLH}-t_{PHL} $ )         Enable Time Z to Low         Disable Time High to Z         Disable Time Low to Z         Maximum Ratings"are those values beyond whind at these limits. The tables of "Electrical Charact to device pins is defined as positive. Current out o         Ind $\Delta  V_{OS} $ are changes in magnitude of $V_{T1}$ and is are given for $V_{CC} = 5.0V$ and $T_A = +25^{\circ}C$ .         d parameter limits specified as an algebraic value s defined as $V_{HST} = V_{TL} - V_{TL}$ .	Diff. Rise Time       RL = 27 $\Omega$ , CL = 15 pF         Prop. Delay Low to High       RL = 27 $\Omega$ , CL = 15 pF         Prop. Delay High to Low       (Figures 6, 7)         Enable Time Z to High       RL = 110 $\Omega$ Enable Time Z to Low       CL = 50 pF         Disable Time High to Z       (Figure 8 - Figure 11)         Disable Time Low to Z       Prop. Delay Low to High         Prop. Delay Low to High       VID = -1.5V to +1.5V         Prop. Delay Low to High       VID = -1.5V to +1.5V         Skew (ItPLH-TeHLI)       (Figures 13, 14)         Enable Time Z to High       CL = 15 pF         Enable Time Z to Low       (Figures 15, 16)         Disable Time Low to Z       Insamm Ratings"are those values beyond which the safety of the device cannol d at these limits. The tables of "Electrical Characteristics" specify conditions for de to device pins is defined as positive. Current out of device pins is defined as negative.         and $\Delta  V_{OS} $ are changes in magnitude of VT1 and VOS, respectively, that occur where are given for V CC = 5.0V and TA = +25'C.         d parameter limits specified as an algebraic value rather than by magnitude.	Diff. Rise Time       Image: Constraint of the state of the device cannot be guaranteed of the device pins is defined as positive. Current out of device pins is defined as positive. Current out of device pins is defined as positive. Current out out an algebraic value rather than by magnitude. s defined as $V_{HST} = V_{TH} - V_{TL}$ .	Diff. Rise Time       Image: Constraint of the state of	Diff. Fise Time12Diff. Fall Time12Prop. Delay Low to High $R_L = 27\Omega$ , $C_L = 15 \text{ pF}$ 22Prop. Delay High to Low( <i>Figures 6, 7</i> )22Enable Time Z to High $R_L = 110\Omega$ 32Enable Time Z to Low $C_L = 50 \text{ pF}$ 32Disable Time High to Z( <i>Figure 8 – Figure 11</i> )22Disable Time Low to Z16ARACTERISTICSProp. Delay High to Low $C_L = 15 \text{ pF}$ Prop. Delay High to Low $C_L = 15 \text{ pF}$ 15Skew ( $ t_{PLH}-t_{PHL} $ )( <i>Figures 13, 14</i> )2Enable Time Z to High $C_L = 15 \text{ pF}$ 15Enable Time Z to Low( <i>Figures 15, 16</i> )17Disable Time Low to Z19Maximum Ratings"are those values beyond which the safety of the device cannot be guaranteed. They are not meant d at these limits. The tables of "Electrical Characteristics" specify conditions for device operation.to device pins is defined as positive. Current out of device pins is defined as nagative. All voltages are referenced to groundand $\Delta  V_{OS} $ are changes in magnitude of $V_{T1}$ and $V_{OS}$ , respectively, that occur when the input changes state.Is are given for V $_{CC} = 5.0V$ and $T_A = +25^{\circ}C$ .defined as $V_{HST} = V_{TL} - V_{TL}$ .	Diff. Hise Time1250Diff. Fall Time1250Prop. Delay Low to High $R_L = 27\Omega$ , $C_L = 15 pF$ 22Prop. Delay High to Low( <i>Figures 6, 7</i> )22Enable Time Z to High $R_L = 110\Omega$ 32Enable Time Z to Low $C_L = 50 pF$ 32Disable Time Low to Z( <i>Figure 8 – Figure 11</i> )22Disable Time Low to Z16Disable Time Z to High $V_{ID} = -1.5V$ to $+1.5V$ 15400 C L = 15 pF1540Prop. Delay Low to High $V_{ID} = -1.5V$ to $+1.5V$ 15400 C L = 15 pF1542Prop. Delay Low to High $V_{ID} = -1.5V$ to $+1.5V$ 15400 C L = 15 pF1550Enable Time Z to High $C_L = 15 pF$ 15Enable Time Z to High $C_L = 15 pF$ 15501750Disable Time Low to Z( <i>Figures 15, 16</i> )17501950Naximum Ratings"are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that d at these limits. The tables of "Electrical Characteristics" specify conditions for device operation.to device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground unless otheund $\Delta  V_{OS} $ are changes in magnitude of $V_{T1}$ and $V_{OS}$ , respectively, that occur when the input changes state.Is are given for $V_{CC} = 5.0V$ and $T_A = +25^{\circ}$ .J parameter limits specified as an algebraic value rather than by magnitude.s defined as $V_{HST} = V_{TL} - V_{TL}$

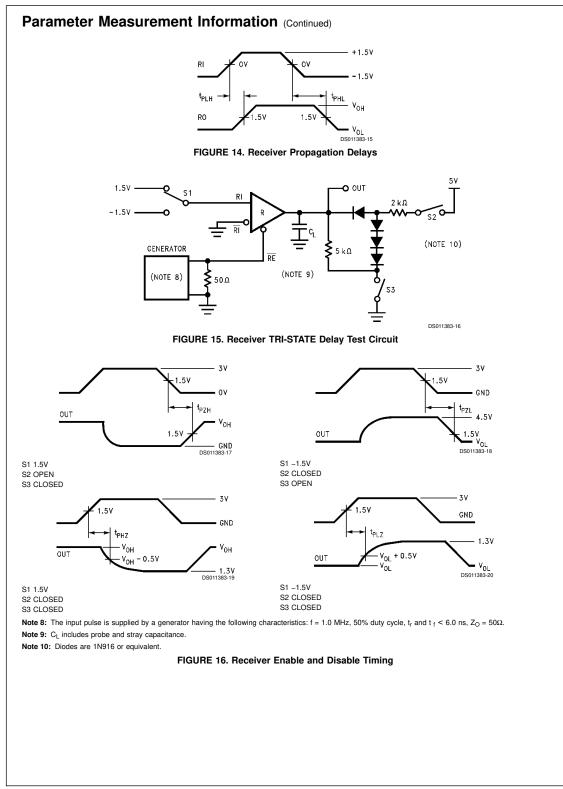
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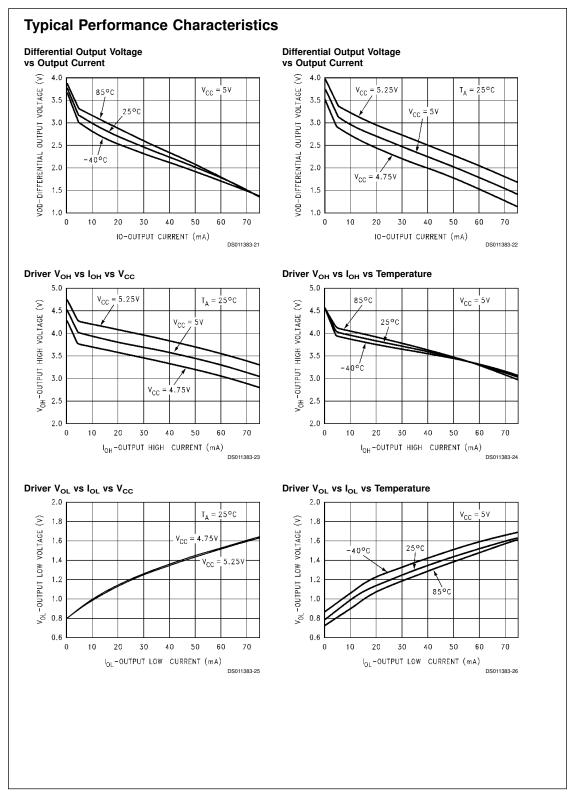




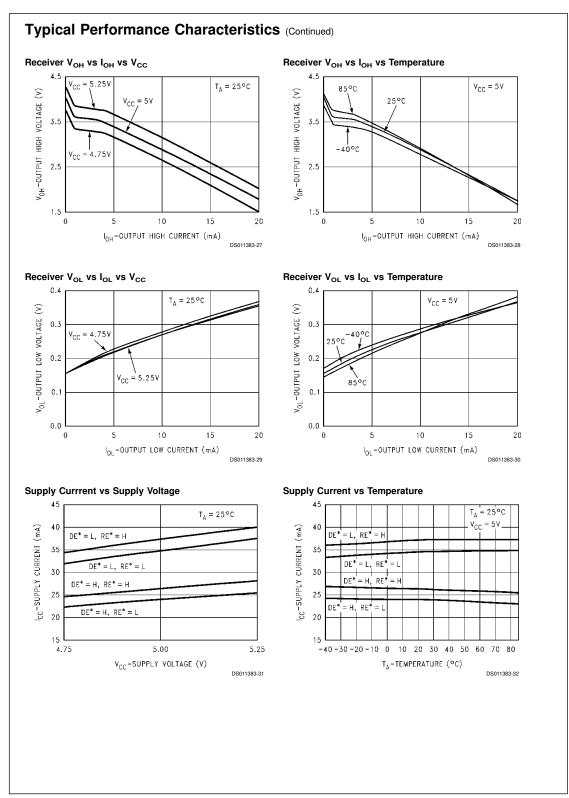


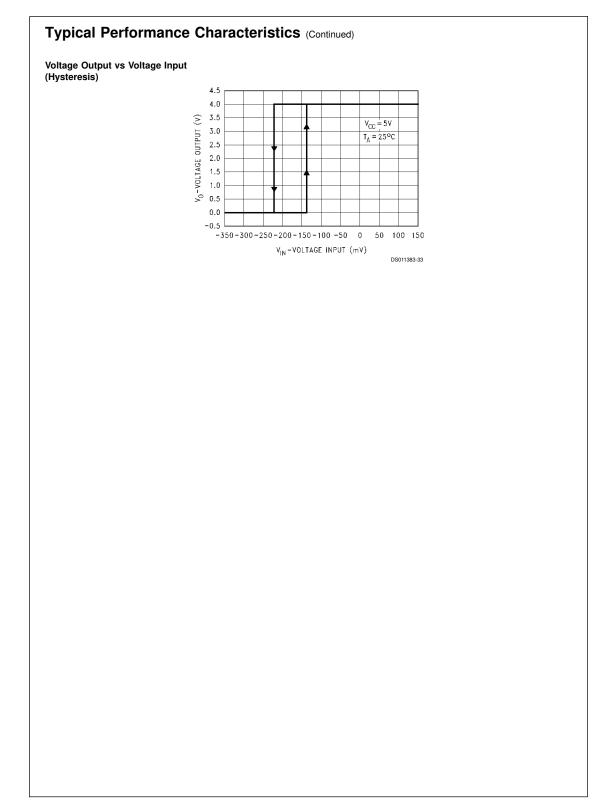
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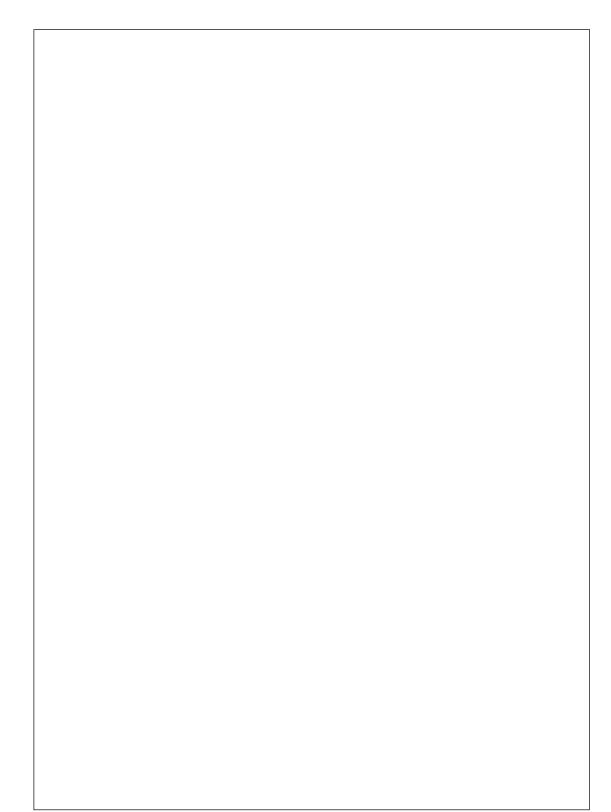


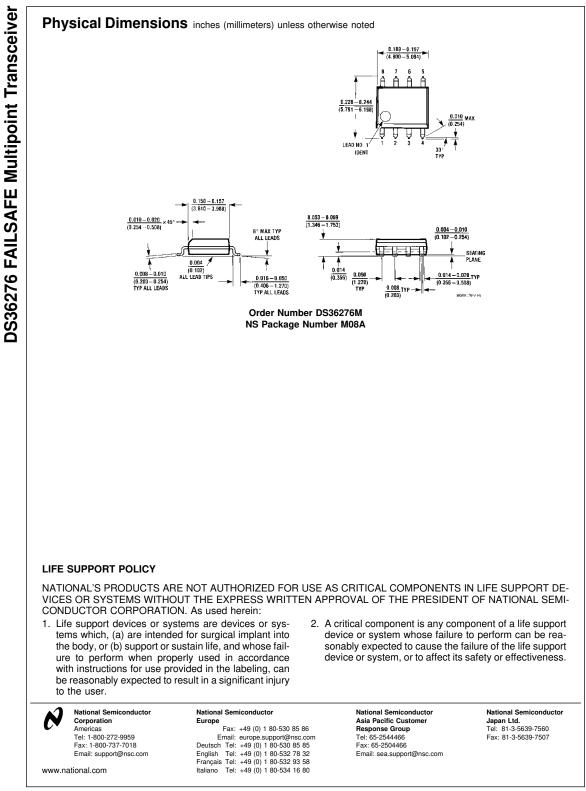


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Product Folder

### DS36276 FailSafe Multipoint Transceiver

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## **General Description**

The DS36276 FAILSAFE Multipoint Transceiver is designed for use on bi-directional differential busses. It is compatible with existing TIA/EIA-485 transceivers, however, it offers an additional feature not supported by standard transceivers.

The FAILSAFE feature guarantees the receiver output to a known state when the Interface is in the following conditions: Floating Line, Idle Line (no active drivers), and Line Fault conditions (open or short). The receiver output is in a HIGH state for the following conditions: OPEN Inputs, Terminated Inputs (50 Ohm), and SHORTED Inputs.

FAILSAFE is a highly desirable feature when the transceivers are used with Asynchronous Controllers such as UARTs.

### **Features**

- FAILSAFE receiver, RO = HIGH for:
  - O OPEN inputs
  - Terminated inputs
  - SHORTED inputs
- Compatible with popular interface standards:
  - o TIA/EIA-485 (RS-485)
  - o TIA/EIA-422-A (RS-422-A)
  - o CCITT Recommendation V.11
- Bi-Directional Transceiver
  - o Designed for multipoint transmission

Parametric Table						
Number of Drivers	1					
Number of Receivers	1					
Supply Voltage	5 V					
Process	Bipolar					

National P/N DS36276 - FailSafe Multipoint Transceiver

- Separate driver input, driver enable, receiver enable, and receiver output for maximum flexibility
- Wide bus common mode range
  - (-7V to +12V)
- Pin compatible with: DS75176B, DS96176, DS3695 and SN75176A and B
- Available in SOIC package

### Datasheet

Title	Size (in Kbytes)	Date	View Online	Download	Receive via Email
DS36276 FAILSAFE Multipoint Transceiver	236 Kbytes	4-Mar-99	View Online	Download	<u>Receive via</u> <u>Email</u>
DS36276 FAILSAFE Multipoint Transceiver (JAPANESE)	431 Kbytes		View Online	Download	Receive via Email

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# Package Availability, Models, Samples & Pricing

Part Number	Package		Status	Mod	Models Samples &		Budgetar	y Pricing	Std Pack	Package
	Туре	# pins		SPICE	IBIS	Electronic Orders	Quantity	\$US each		<b>Marking</b>
DS36276M	SOIC NARROW	8	Full production	N/A	N/A	24 Hour Samples	1K+	\$1.3400	tube of	[logo]¢2¢T DS36
				1,711		Buy Now		<i>410</i> 100	95	276M
DS36276MX	SOIC NARROW	8	Full production	N/A	N/A		1K+	\$1.3400	reel of 2500	[logo]¢2¢T DS36 276M
DS36276 MDC	Die		Full production	N/A	N/A				tray of N/A	-

## **Application Notes**

Title	Size (in Kbytes)	Date	View Online	Download	Receive via Email
<b>AN-1057:</b> Application Note 1057 Ten Ways to Bulletproof RS-485 Interfaces	155 Kbytes	5-Oct-98	View Online	Download	Receive via Email
AN-1031: Application Note 1031 TIA/EIA-422-B Overview	101 Kbytes	3-Feb-00	View Online	Download	Receive via Email

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